

**NPN SILICON PLANAR MEDIUM POWER TRANSISTORS IN SOT89**

## Features

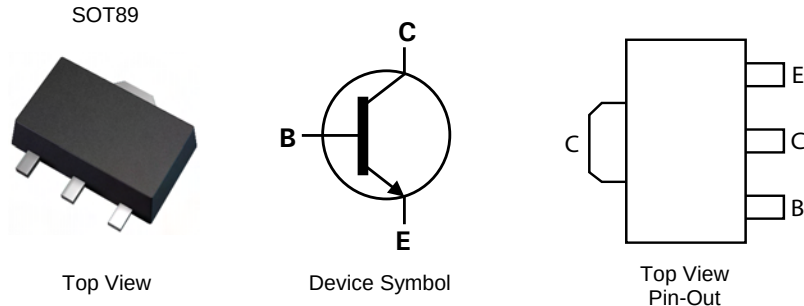
- $I_C = 1A$  Continuous Collector Current
- Low Saturation Voltage  $V_{CE(sat)} < 500mV @ 0.5A$
- Gain Groups 10 and 16
- Epitaxial Planar Die Construction
- Complementary PNP types: BCX51, 52, and 53
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP capable (Note 4)**

## Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Leads, Solderable per MIL-STD-202 Method 208 
- Weight: 0.072 grams (Approximate)

## Applications

- Medium Power Switching or Amplification Applications
- AF driver and output stages

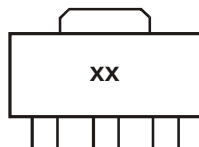


## Ordering Information (Notes 4 & 5)

| Product     | Compliance | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|-------------|------------|---------|--------------------|-----------------|-------------------|
| BCX54TA     | AEC-Q101   | BA      | 7                  | 12              | 1,000             |
| BCX5410TA   | AEC-Q101   | BC      | 7                  | 12              | 1,000             |
| BCX5416TA   | AEC-Q101   | BD      | 7                  | 12              | 1,000             |
| BCX5416-13R | AEC-Q101   | BD      | 13                 | 12              | 4,000             |
| BCX55TA     | AEC-Q101   | BE      | 7                  | 12              | 1,000             |
| BCX5510TA   | AEC-Q101   | BG      | 7                  | 12              | 1,000             |
| BCX5516TA   | AEC-Q101   | BM      | 7                  | 12              | 1,000             |
| BCX56TA     | AEC-Q101   | BH      | 7                  | 12              | 1,000             |
| BCX5610TA   | AEC-Q101   | BK      | 7                  | 12              | 1,000             |
| BCX5616TA   | AEC-Q101   | BL      | 7                  | 12              | 1,000             |
| BCX5616QTA  | Automotive | BL      | 7                  | 12              | 1,000             |
| BCX5616TC   | AEC-Q101   | BL      | 13                 | 12              | 4,000             |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
  3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
  5. For packaging details, go to our website at <http://www.diodes.com>

## Marking Information



xx = Product Type Marking Code, as follows:

|              |              |              |
|--------------|--------------|--------------|
| BCX54 = BA   | BCX55 = BE   | BCX56 = BH   |
| BCX5410 = BC | BCX5510 = BG | BCX5610 = BK |
| BCX5416 = BD | BCX5516 = BM | BCX5616 = BL |

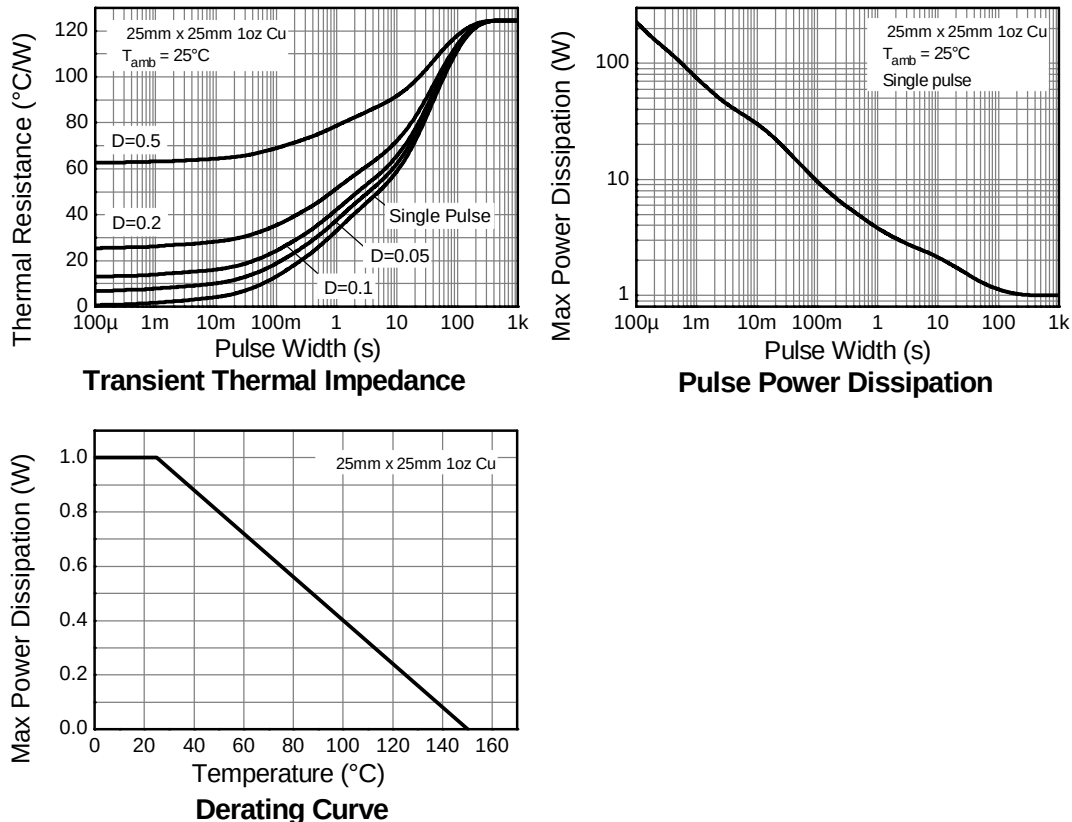
**Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

| Characteristic               | Symbol           | BCX54 | BCX55 | BCX56 | Unit |
|------------------------------|------------------|-------|-------|-------|------|
| Collector-Base Voltage       | V <sub>CBO</sub> | 45    | 60    | 100   | V    |
| Collector-Emitter Voltage    | V <sub>CEO</sub> | 45    | 60    | 80    | V    |
| Emitter-Base Voltage         | V <sub>EBO</sub> | 6     |       |       | V    |
| Continuous Collector Current | I <sub>C</sub>   | 1     |       |       | A    |
| Peak Pulse Collector Current | I <sub>CM</sub>  | 1.5   |       |       |      |
| Continuous Base Current      | I <sub>B</sub>   | 100   |       |       | mA   |
| Peak Pulse Base Current      | I <sub>BM</sub>  | 200   |       |       |      |

**Thermal Characteristics**

| Characteristic                                   | Symbol          | Value       | Unit               |
|--------------------------------------------------|-----------------|-------------|--------------------|
| Power Dissipation (Note 6)                       | $P_D$           | 1           | W                  |
| Thermal Resistance, Junction to Ambient (Note 6) | $R_{\theta JA}$ | 124         | $^\circ\text{C/W}$ |
| Thermal Resistance, Junction to Leads (Note 7)   | $R_{\theta JL}$ | 10.0        | $^\circ\text{C/W}$ |
| Operating and Storage Temperature Range          | $T_J, T_{STG}$  | -65 to +150 | $^\circ\text{C}$   |

Notes: 6. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.  
 7. Thermal resistance from junction to solder-point (on the exposed collector pad).

**Thermal Characteristics**


**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

| Characteristic                                 |              | Symbol        | Min | Typ | Max       | Unit          | Test Condition                                                           |
|------------------------------------------------|--------------|---------------|-----|-----|-----------|---------------|--------------------------------------------------------------------------|
| Collector-Base Breakdown Voltage               | BCX54        | $BV_{CBO}$    | 45  | —   | —         | V             | $I_C = 100\mu\text{A}$                                                   |
|                                                | BCX55        |               | 60  |     |           |               |                                                                          |
|                                                | BCX56        |               | 100 |     |           |               |                                                                          |
| Collector-Emitter Breakdown Voltage (Note 8)   | BCX54        | $BV_{CEO}$    | 45  | —   | —         | V             | $I_C = 10\text{mA}$                                                      |
|                                                | BCX55        |               | 60  |     |           |               |                                                                          |
|                                                | BCX56        |               | 80  |     |           |               |                                                                          |
| Emitter-Base Breakdown Voltage                 |              | $BV_{EBO}$    | 6   | —   | —         | V             | $I_E = 100\mu\text{A}$                                                   |
| Collector Cut-off Current                      |              | $I_{CBO}$     | -   | —   | 0.1<br>20 | $\mu\text{A}$ | $V_{CB} = 30\text{V}$<br>$V_{CB} = 30\text{V}, T_A = +150^\circ\text{C}$ |
| Emitter Cut-off Current                        |              | $I_{EBO}$     | -   | —   | 20        | nA            | $V_{EB} = 5\text{V}$                                                     |
| Static Forward Current Transfer Ratio (Note 6) | All versions | $h_{FE}$      | 25  | —   | -         | —             | $I_C = 5\text{mA}, V_{CE} = 2\text{V}$                                   |
|                                                |              |               | 40  | —   | 250       |               | $I_C = 150\text{mA}, V_{CE} = 2\text{V}$                                 |
|                                                | 10 gain grp  |               | 25  | —   | -         |               | $I_C = 500\text{mA}, V_{CE} = 2\text{V}$                                 |
|                                                | 16 gain grp  |               | 63  | —   | 160       |               | $I_C = 150\text{mA}, V_{CE} = 2\text{V}$                                 |
| Collector-Emitter Saturation Voltage (Note 8)  |              | $V_{CE(sat)}$ | —   | —   | 0.5       | V             | $I_C = 500\text{mA}, I_B = 50\text{mA}$                                  |
| Base-Emitter Turn-On Voltage (Note 8)          |              | $V_{BE(on)}$  | —   | —   | 1.0       | V             | $I_C = 500\text{mA}, V_{CE} = 2\text{V}$                                 |
| Transition Frequency                           |              | $f_T$         | 150 | —   | -         | MHz           | $I_C = 50\text{mA}, V_{CE} = 10\text{V}$<br>$f = 100\text{MHz}$          |
| Output Capacitance                             |              | $C_{obo}$     | —   | —   | 25        | pF            | $V_{CB} = 10\text{V}, f = 1\text{MHz}$                                   |

Notes: 8. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

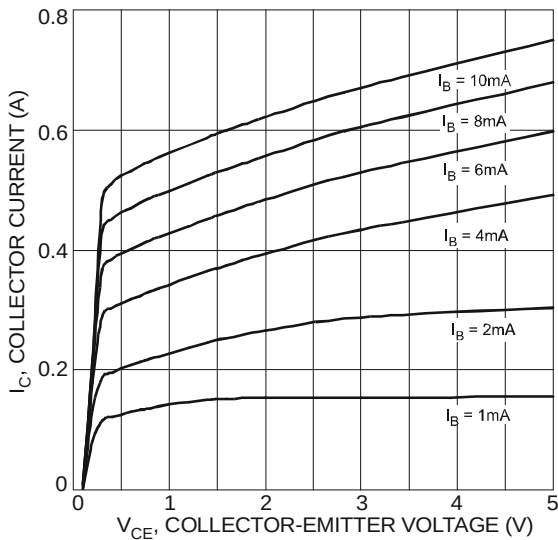


Fig. 1 Typical Collector Current vs. Collector-Emitter Voltage

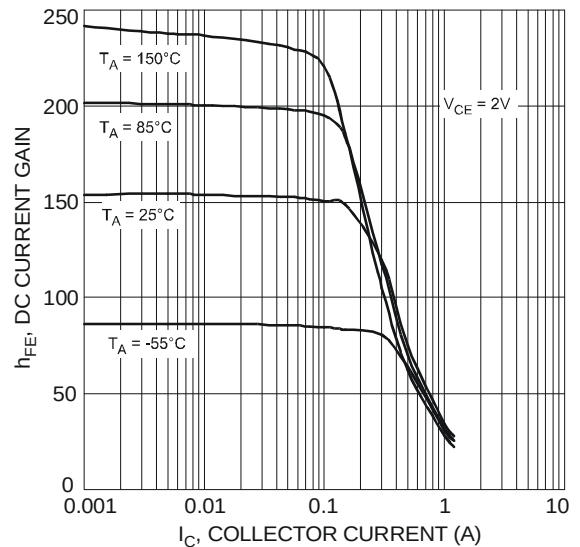


Fig. 2 Typical DC Current Gain vs. Collector Current

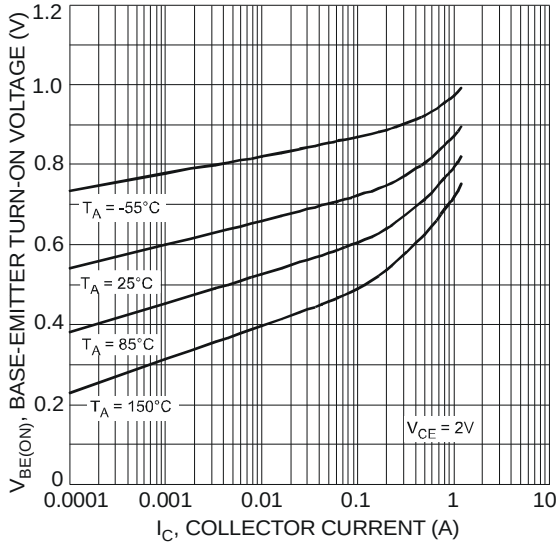


Fig. 3 Typical Base-Emitter Turn-On Voltage vs. Collector Current

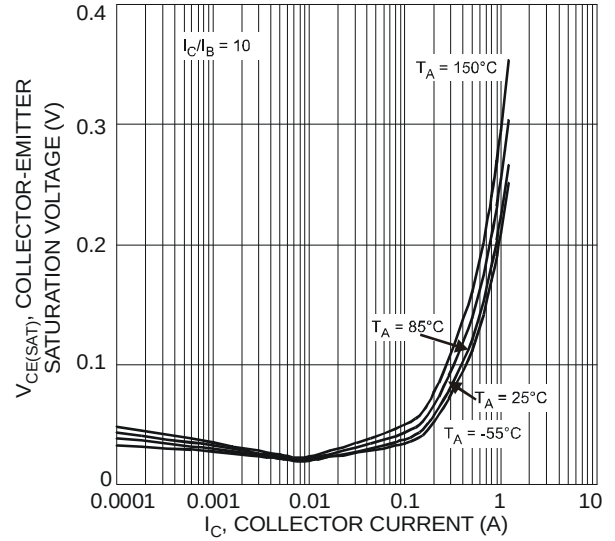


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

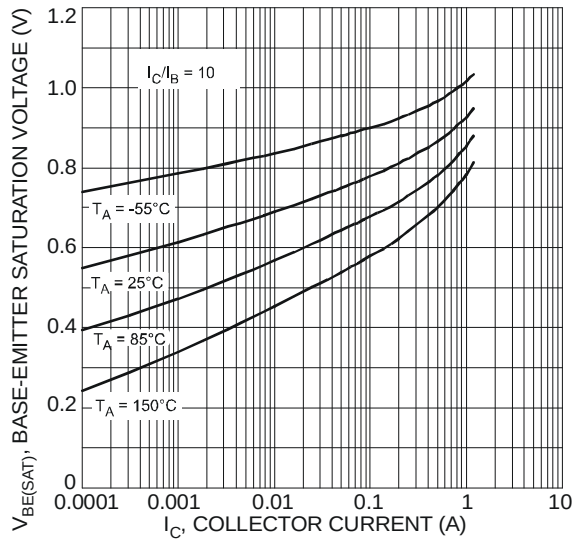


Fig. 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

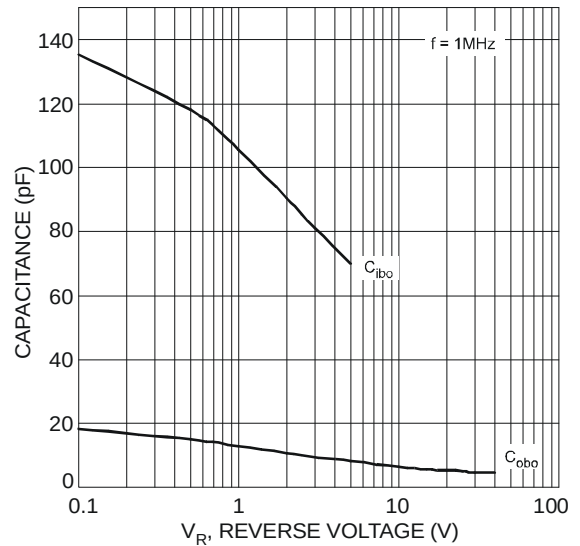


Fig. 6 Typical Capacitance Characteristics

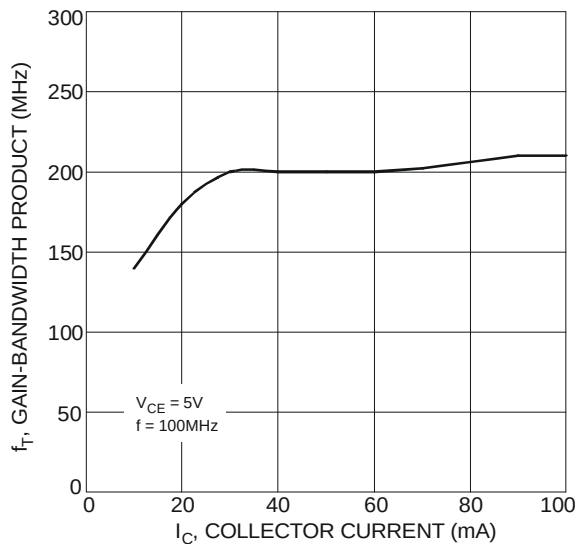
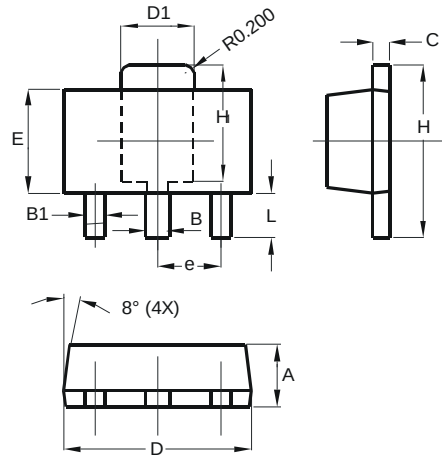


Fig. 7 Typical Gain-Bandwidth Product vs. Collector Current

## Package Outline Dimensions

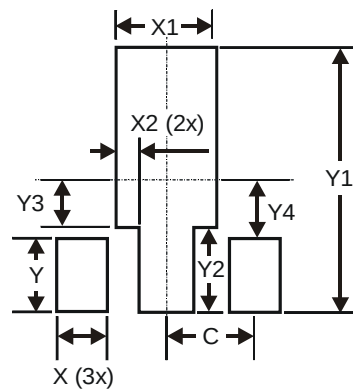
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



| SOT89                |          |      |
|----------------------|----------|------|
| Dim                  | Min      | Max  |
| A                    | 1.40     | 1.60 |
| B                    | 0.44     | 0.62 |
| B1                   | 0.35     | 0.54 |
| C                    | 0.35     | 0.44 |
| D                    | 4.40     | 4.60 |
| D1                   | 1.62     | 1.83 |
| E                    | 2.29     | 2.60 |
| e                    | 1.50 Typ |      |
| H                    | 3.94     | 4.25 |
| H1                   | 2.63     | 2.93 |
| L                    | 0.89     | 1.20 |
| All Dimensions in mm |          |      |

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| X          | 0.900         |
| X1         | 1.733         |
| X2         | 0.416         |
| Y          | 1.300         |
| Y1         | 4.600         |
| Y2         | 1.475         |
| Y3         | 0.950         |
| Y4         | 1.125         |
| C          | 1.500         |

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